

/ Descriptions

TO-252 PNP Silicon PNP transistor in a TO-252 Plastic Package.

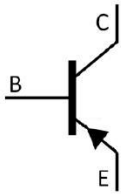
/ Features

Low Speed ,Load Formed for Surface Mount Application.

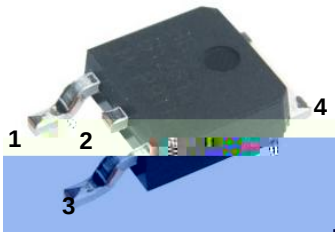
/ Applications

General Purpose Amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

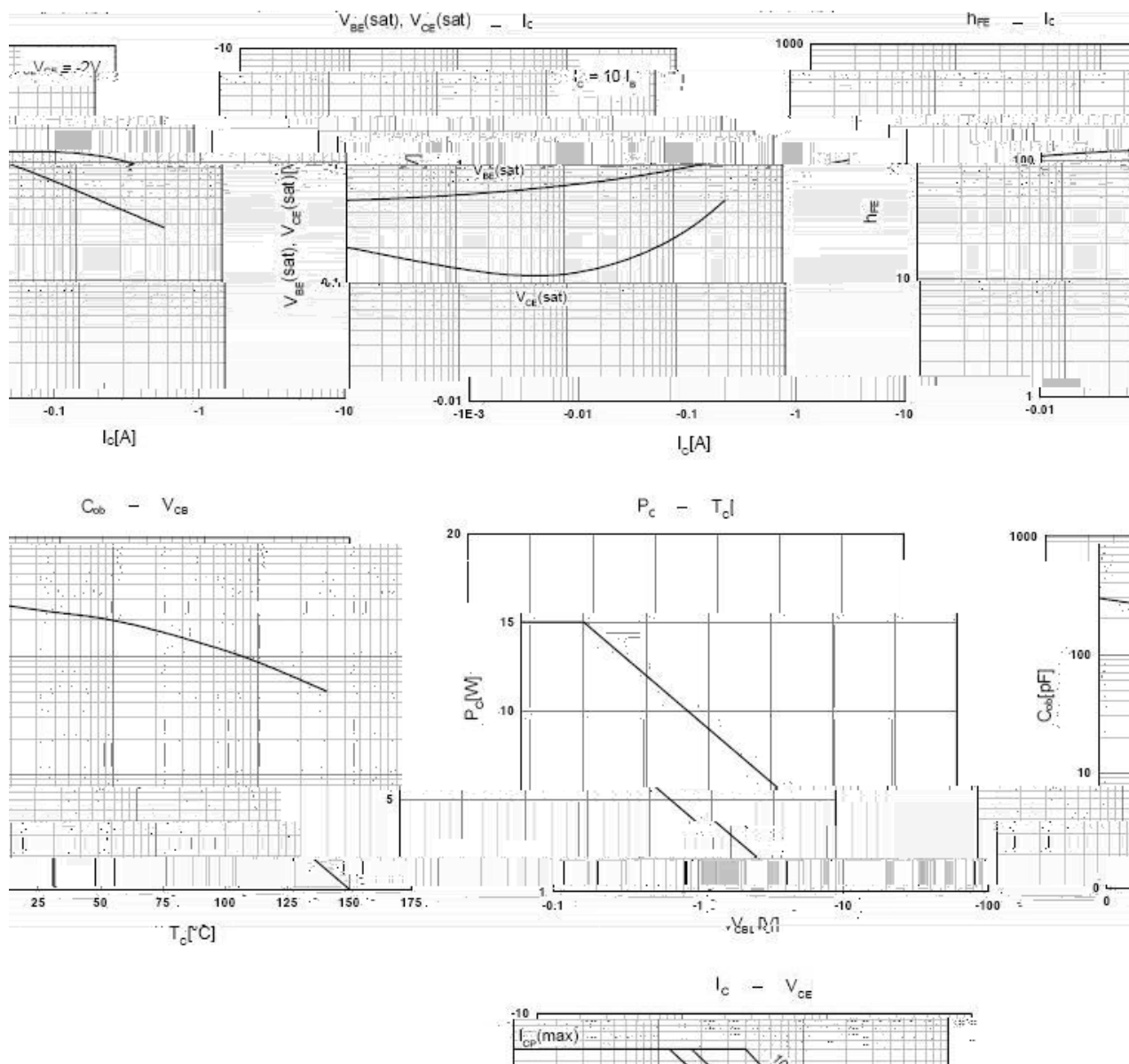
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-5.0	A
Base Current - Continuous	I_B	-1.0	A
Collector Power Dissipation	$P_C(T_C=25)$	15	W
Collector Power Dissipation	P_C	1.56	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-65 150	

/ Electrical Characteristics(Ta=25)

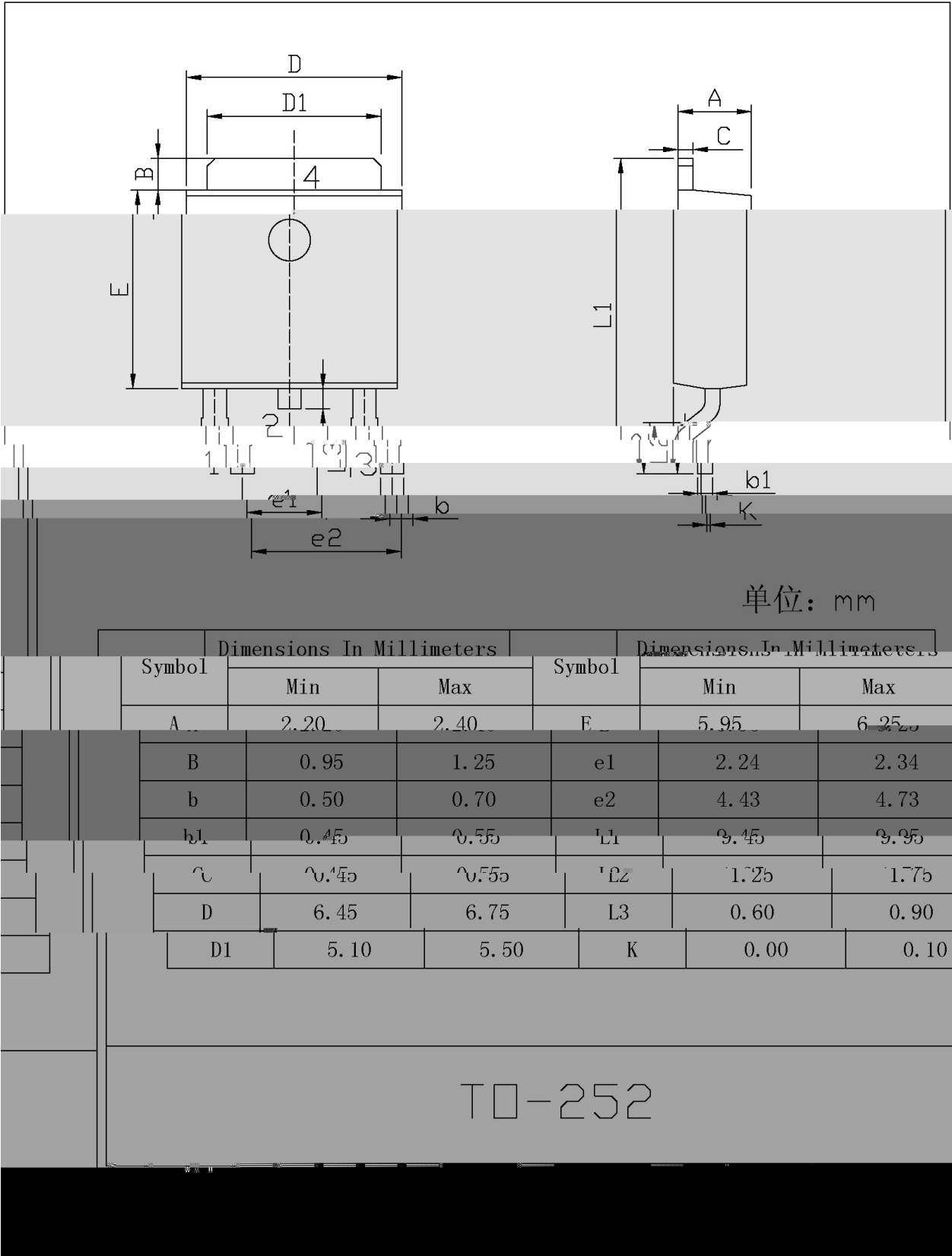
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage*	$*V_{CEO}$	$I_C=-30mA$ $I_B=0$	-100			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-60V$ $I_B=0$			-50	μA
Collector Cut-Off Current	I_{CES}	$V_{CE}=-100V$ $V_{BE}=0$			-20	μA
Emitter Cut-Off Current	I_{EBO}	$V_{BE}=-5.0V$ $I_C=0$			-1.0	mA
DC Current Gain*	$*h_{FE}$	$V_{CE}=-4.0V$ $I_C=-3.0A$	15		75	
Collector to Emitter Saturation Voltage*	$*V_{CE(sat)}$	$I_C=-3.0A$ $I_B=-375mA$			-1.2	V
Base to Emitter On Voltage*	$*V_{BE(on)}$	$V_{CE}=-4.0A$ $I_C=-3.0A$			-1.8	V
Current- Gain Bandwidth Product	f_T	$V_{CE}=-10V$ $I_C=-100mA$	3			MHz

*:pw() $\leq 300\mu s$,duty cycle() $\leq 2\%$.

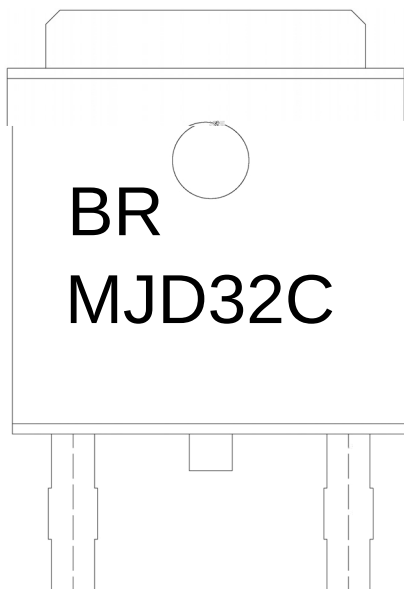
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

MJD32C

Note:

BR: Company Code

MJD32C: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

